



## Description

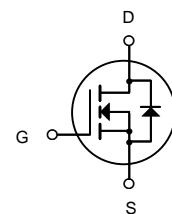
The HBSS138LT3G uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



## General Features

$V_{DS} = 50V$   $I_D = 0.22A$

$R_{DS(ON)} < 2.0\Omega$  @  $V_{GS}=10V$



N-Channel MOSFET

## Application

Battery protection

Load switch

Uninterruptible power supply

## Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
HBSS138LT3G	SOT-23	SS	3000

## Absolute Maximum Ratings ( $T_c=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
$V_{DS}$	Drain-Source Voltage	50	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Continuous Drain Current ( $T_J = 150^\circ C$ )	$T_A = 25^\circ C$	0.22
		$T_A = 100^\circ C$	0.13
$I_{DM}$	Drain Current-Pulsed <sup>(Note 1)</sup>	0.88	A
$P_D$	Maximum Power Dissipation	0.35	W
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	-55 To 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient <sup>(Note 2)</sup>	357	$^\circ C/W$



**Electrical Characteristics ( $T_A=25^\circ\text{C}$  unless otherwise noted)**

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
<b>Off characteristics</b>						
Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_{\text{D}} = 250\mu\text{A}$	50			V
Gate-body leakage	$I_{\text{GSS}}$	$V_{\text{DS}} = 0\text{V}, V_{\text{GS}} = \pm 20\text{V}$			$\pm 100$	nA
Zero gate voltage drain current	$I_{\text{DSS}}$	$V_{\text{DS}} = 50\text{V}, V_{\text{GS}} = 0\text{V}$			0.5	$\mu\text{A}$
		$V_{\text{DS}} = 30\text{V}, V_{\text{GS}} = 0\text{V}$			100	nA
<b>On characteristics</b>						
Gate-threshold voltage (note 1)	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_{\text{D}} = 1\text{mA}$	0.8		1.5	V
Static drain-source on-resistance (note 1)	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 10\text{V}, I_{\text{D}} = 0.22\text{A}$		1.1	2.0	$\Omega$
		$V_{\text{GS}} = 4.5\text{V}, I_{\text{D}} = 0.22\text{A}$		1.5	3	
Forward transconductance (note 1)	$g_{\text{FS}}$	$V_{\text{DS}} = 10\text{V}, I_{\text{D}} = 0.22\text{A}$	0.12			S
<b>Dynamic characteristics (note 2)</b>						
Input capacitance	$C_{\text{iss}}$	$V_{\text{DS}} = 25\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$		27		pF
Output capacitance	$C_{\text{oss}}$			13		
Reverse transfer capacitance	$C_{\text{rss}}$			6		
<b>Switching characteristics</b>						
Turn-on delay time (note 1,2)	$t_{\text{d}(\text{on})}$	$V_{\text{DD}} = 30\text{V}, V_{\text{DS}} = 10\text{V}, I_{\text{D}} = 0.29\text{A}, R_{\text{GEN}} = 6\Omega$			5	ns
Rise time (note 1,2)	$t_r$				18	
Turn-off delay time (note 1,2)	$t_{\text{d}(\text{off})}$				36	
Fall time (note 1,2)	$t_f$				14	
<b>Drain-source body diode characteristics</b>						
Body diode forward voltage (note 1)	$V_{\text{SD}}$	$I_{\text{S}} = 0.44\text{A}, V_{\text{GS}} = 0\text{V}$			1.4	V

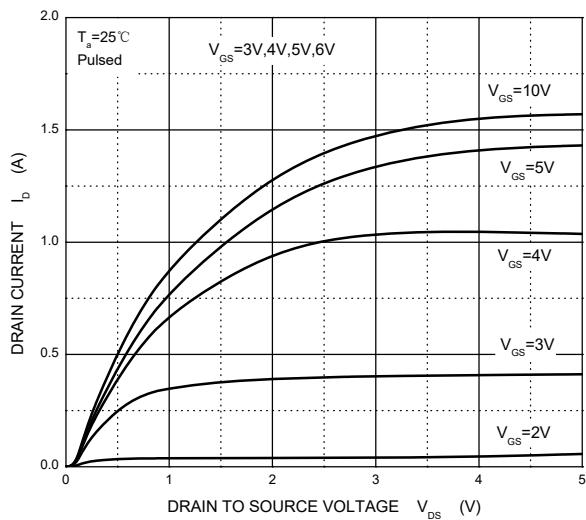
**Notes:**

1. Pulse Test ; Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .
2. These parameters have no way to verify.

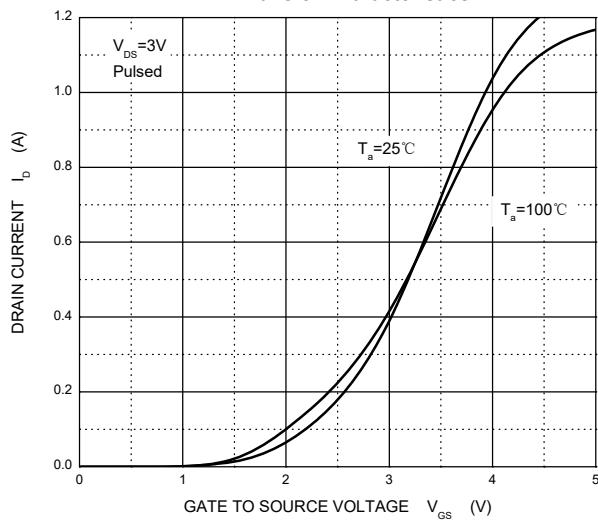


## Typical Characteristics

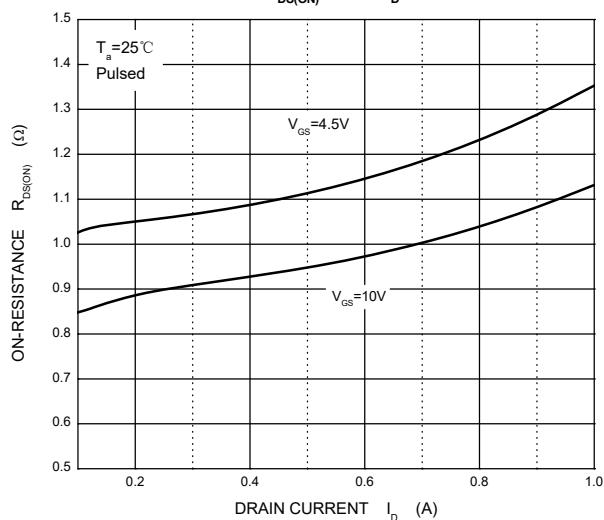
Output Characteristics



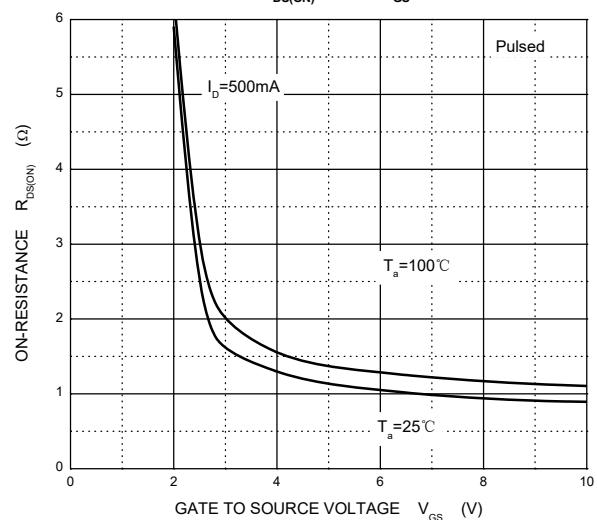
Transfer Characteristics



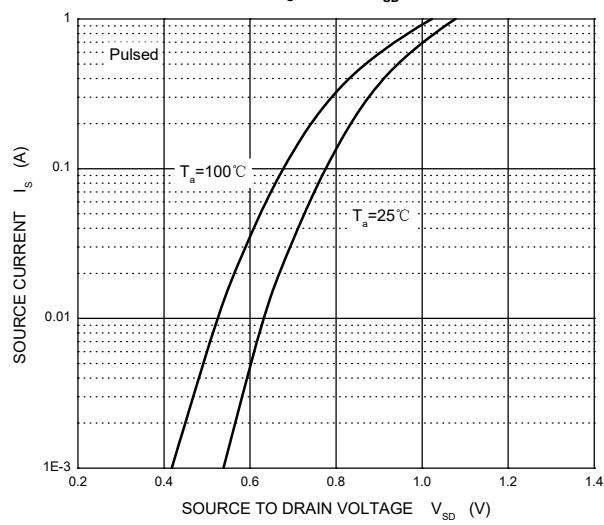
$R_{DS(ON)}$  —  $I_D$



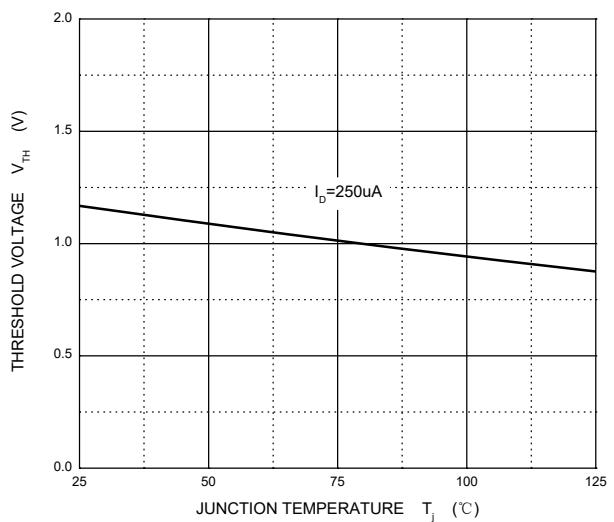
$R_{DS(ON)}$  —  $V_{GS}$



$I_s$  —  $V_{SD}$

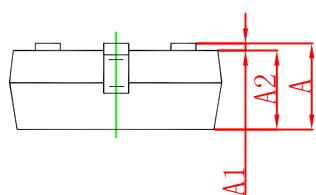
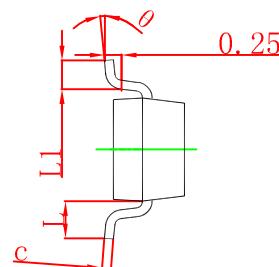
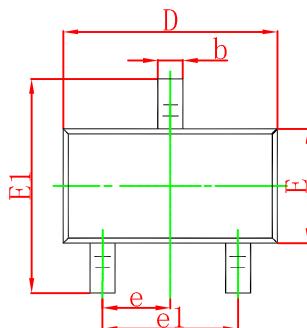


Threshold Voltage



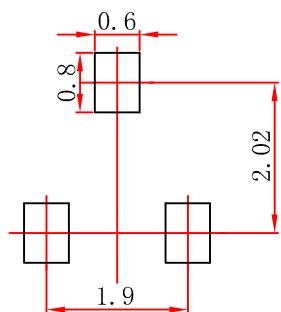


## SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
$\theta$	0°	8°	0°	8°

## SOT-23 Suggested Pad Layout



### Note:

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.05$ mm.
3. The pad layout is for reference purposes only.



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